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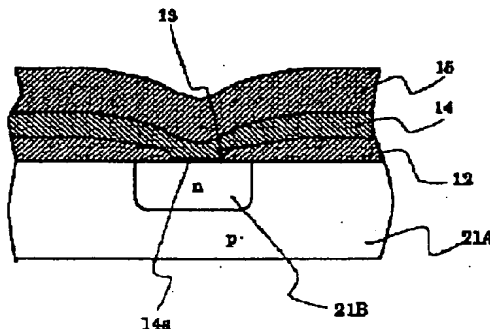
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(54) **SCHOTTKY BARRIER SEMICONDUCTOR  
DEVICE AND MANUFACTURE THEREOF**

(57) Abstract:

**PROBLEM TO BE SOLVED:** To provide a schottky barrier semiconductor device and a method of manufacturing the same which has a low self-loss and totally different characteristics from those of a schottky diode.

**SOLUTION:** A schottky barrier semiconductor device is provided with a schottky barrier layer which forms a schottky barrier in contact with a semiconductor layer on the surface of the silicon semiconductor layer. The schottky barrier layer comprises a titanium layer 14 having at least titanium silicide 14a at a plane contacting the semiconductor layer, and a titanium nitride layer 15 is formed on the schottky barrier layer.



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